

Title (en)

SELF-ORGANIZED PIN-TYPE NANOSTRUCTURES, AND PRODUCTION THEREOF ON SILICON

Title (de)

SELBSTORGANISIERTE NADELARTIGE NANO-STRUKTUREN UND IHRE HERSTELLUNG AUF SILIZIUM

Title (fr)

NANOSTRUCTURES EN AIGUILLES AUTO-ORGANISEES ET LEUR PRODUCTION SUR DU SILICIUM

Publication

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Application

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Abstract (en)

[origin: WO2007042520A2] According to the invention, a self-organized pin-type structure (4, 4a) that has no crystal defects, a great aspect ratio, and nano dimensions is produced on the surface of silicon wafers with the aid of an RIE etching process for silicon (3) by selecting the gas concentration of the etching plasma, without taking any additional structuring measure (e-beam, interference lithography, or others), thus obtaining broadband antireflection that can be used in many different ways.

IPC 8 full level

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